

SANYO

No.3702A

2SC4633

NPN Triple Diffused Planar Silicon Transistor
**High-Voltage Amp,
 High-Voltage Switching Applications**

Features

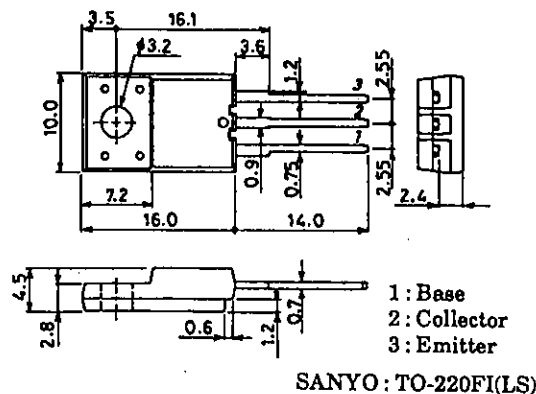
- High breakdown voltage ($V_{CEO \text{ min}} = 1200\text{V}$).
- Small Cob (typical Cob = 2.0pF).
- Full-isolation package.
- High reliability (Adoption of HVP process).

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CBO}	1500	V
Collector-to-Emitter Voltage	V_{CEO}	1200	V
Emitter-to-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	30	mA
Collector Current (Pulse)	I_{CP}	100	mA
Collector Dissipation	P_C	2	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

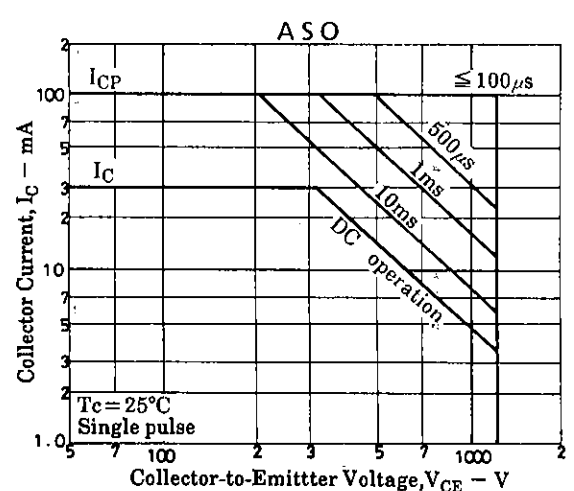
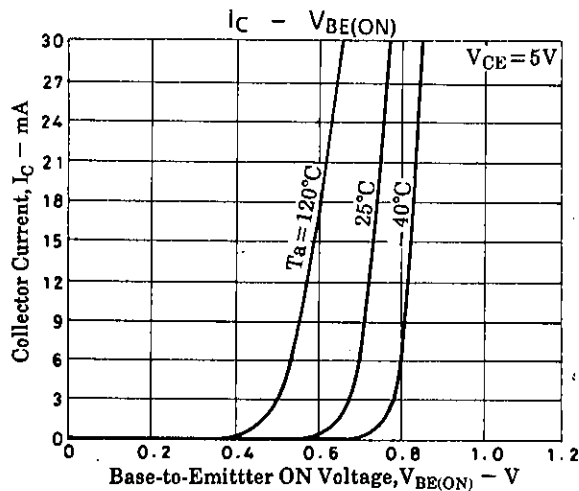
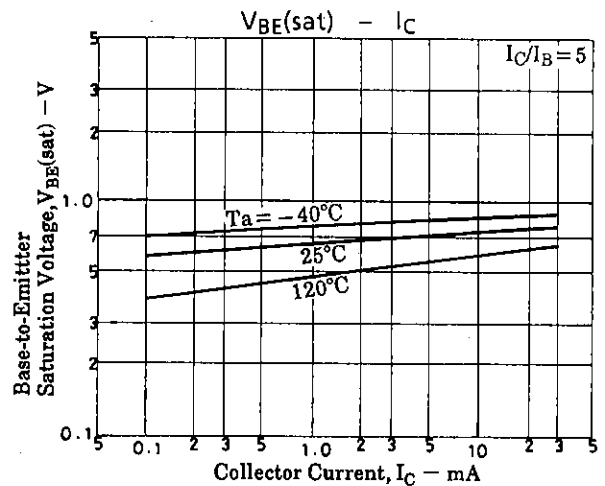
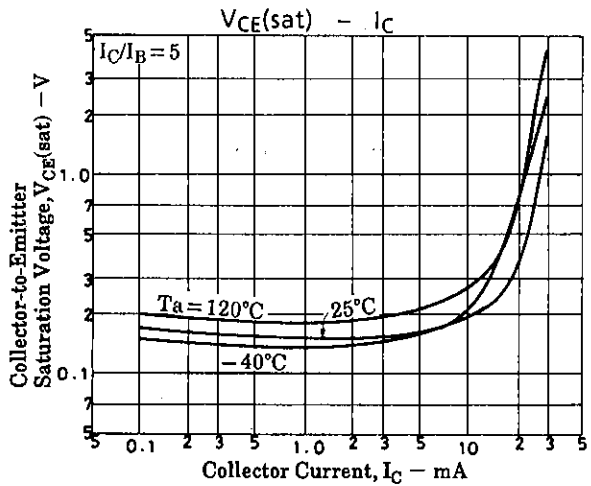
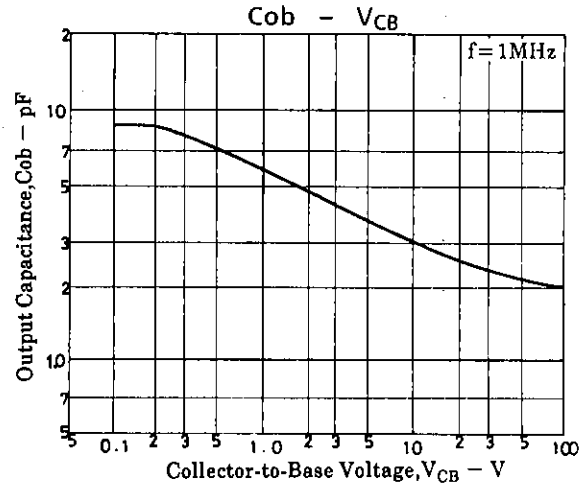
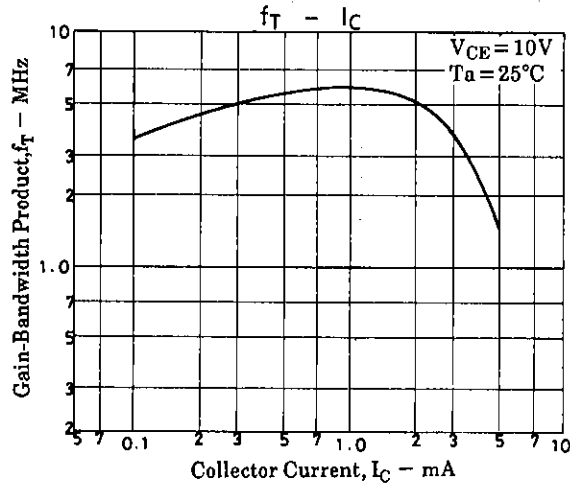
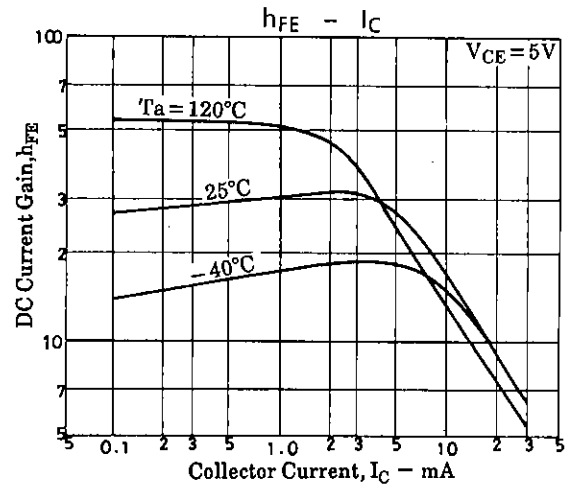
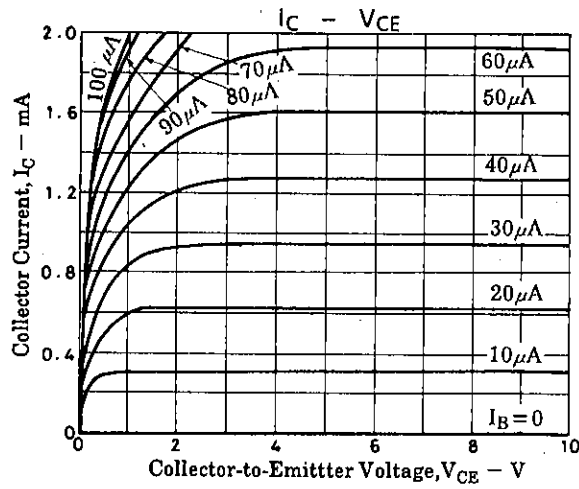
Electrical Characteristics at $T_a = 25^\circ\text{C}$

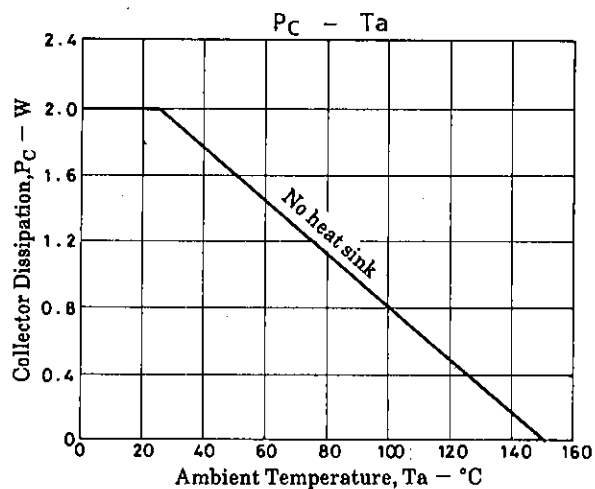
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 1200\text{V}, I_E = 0$			1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 1.5\text{mA}$	10		60	
Gain-Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 1.5\text{mA}$		6		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 3\text{mA}, I_B = 0.6\text{mA}$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 3\text{mA}, I_B = 0.6\text{mA}$			2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	1500			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	1200			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	5			V
Output Capacitance	Cob	$V_{CB} = 100\text{V}, f = 1\text{MHz}$		2.0		pF
Thermal Resistance	R_{thj-c}	Junction - case			8.3	$^\circ\text{C/W}$

Package Dimensions 2079B
 (unit : mm)

SANYO Electric Co., Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

80296YK (KOTO) TA-0465, AX-7506, 8-6924 No.3702-1/3





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